

TK70D06J1

Switching Regulator Application

- High-Speed switching
- Small gate charge: $Q_g = 87\text{nC}$ (typ.)
- Low drain-source ON resistance: $R_{DS(ON)} = 5.1\text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 80\text{S}$
- Low leakage current: $I_{DSS} = 10\text{ }\mu\text{A}$ (max) ($V_{DS} = 60\text{ V}$)
- Enhancement-mode: $V_{th} = 1.1\sim 2.3\text{ V}$ ($V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	60	V
Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)		V_{DGR}	60	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	70	A
	Pulse (Note 1)	I_{DP}	280	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	140	W
Single pulse avalanche energy (Note 2)		E_{AS}	751	mJ
Avalanche current		I_{AR}	70	A
Repetitive avalanche energy (Note 3)		E_{AR}	10.3	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	$-55\sim 150$	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.89	$^\circ\text{C/W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	83.3	$^\circ\text{C/W}$

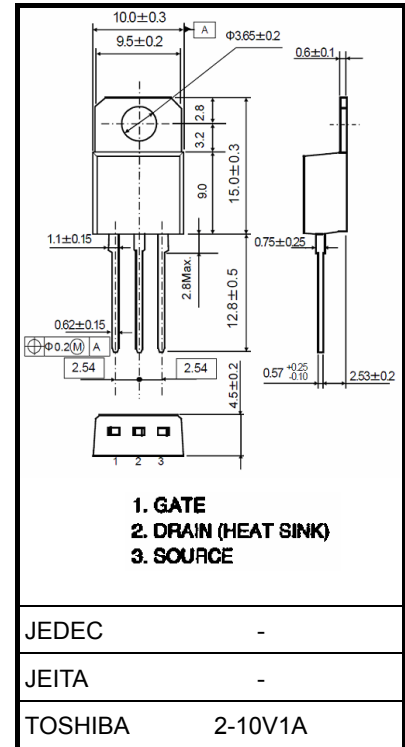
Note 1: Ensure that the channel & lead temperature does not exceed 150°C .

Note 2: $V_{DD} = 25\text{ V}$, $T_{ch} = 25^\circ\text{C}$, $L = 200\text{ }\mu\text{H}$, $I_{AR} = 70\text{ A}$, $R_G = 1\text{ }\Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature.

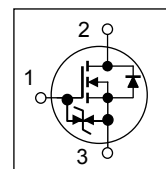
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 1.35 g (typ.)

Internal Connection



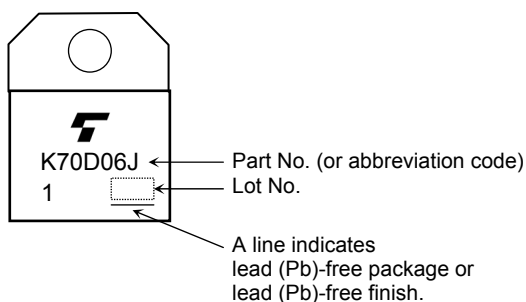
Electrical Characteristics (Ta = 25°C)

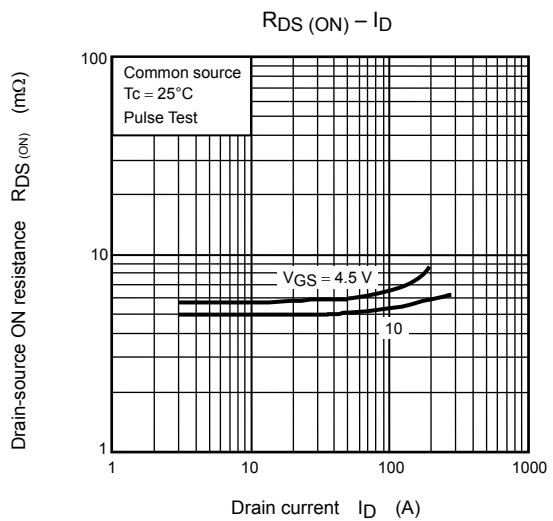
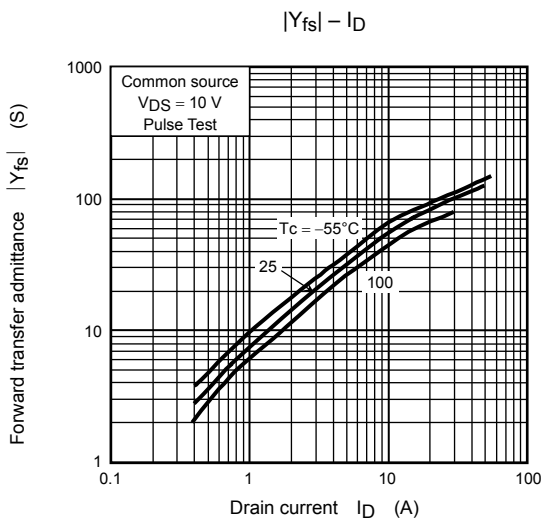
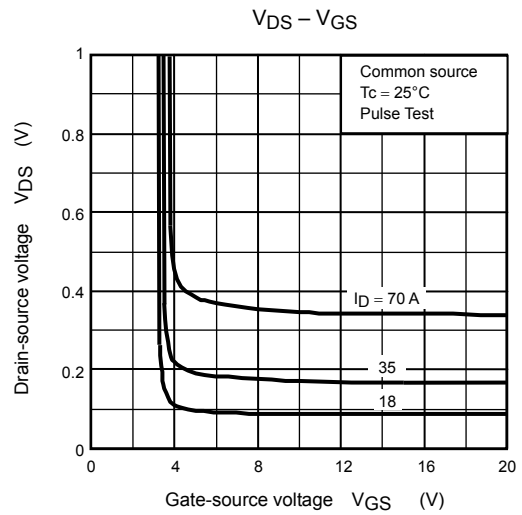
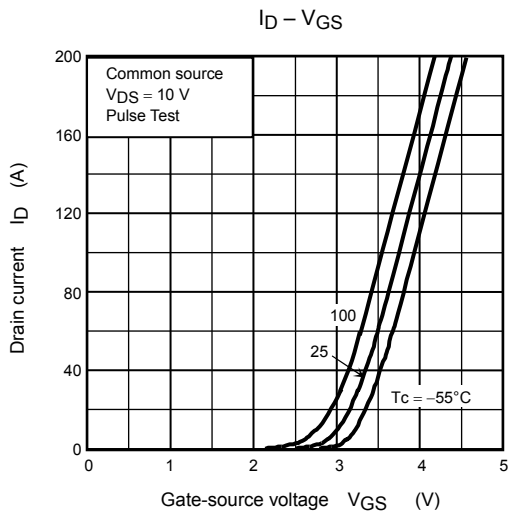
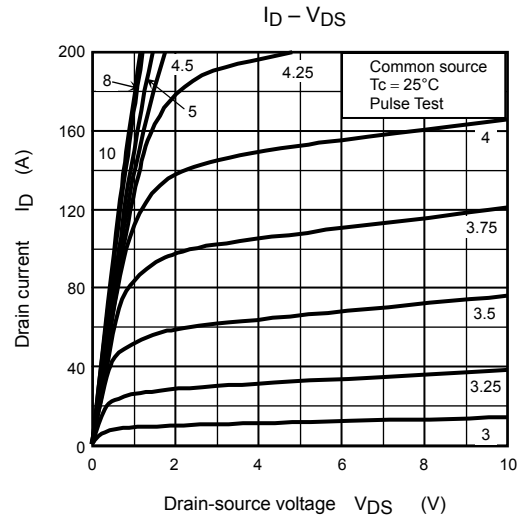
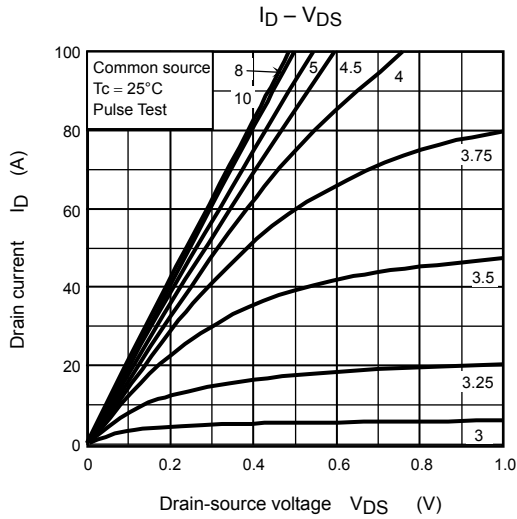
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	60	—	—	V
		$V_{(BR) DSX}$	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	45	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.1	—	2.3	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4.5 \text{ V}, I_D = 35 \text{ A}$	—	5.8	7.6	m Ω
			$V_{GS} = 10 \text{ V}, I_D = 35 \text{ A}$	—	5.1	6.4	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 35 \text{ A}$	40	80	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	5450	—	pF
Reverse transfer capacitance		C_{rss}		—	320	—	
Output capacitance		C_{oss}		—	1420	—	
Switching time	Rise time	t_r	<p>Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$</p>	—	9	—	ns
	Turn-ON time	t_{on}		—	24	—	
	Fall time	t_f		—	21	—	
	Turn-OFF time	t_{off}		—	106	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 48 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 70 \text{ A}$	—	47	—	nC
			$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 70 \text{ A}$	—	87	—	
Gate-source charge 1		Q_{gs1}	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 70 \text{ A}$	—	16	—	
Gate-drain ("miller") charge		Q_{gd}		—	19	—	
Gate switch charge		Q_{sw}		—	30	—	

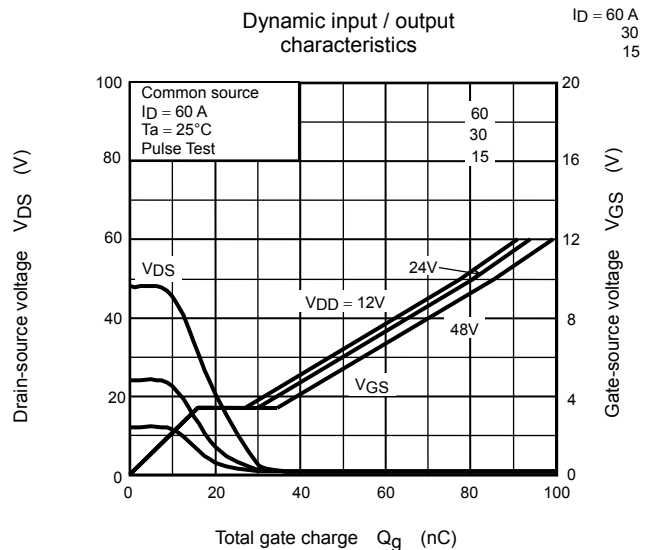
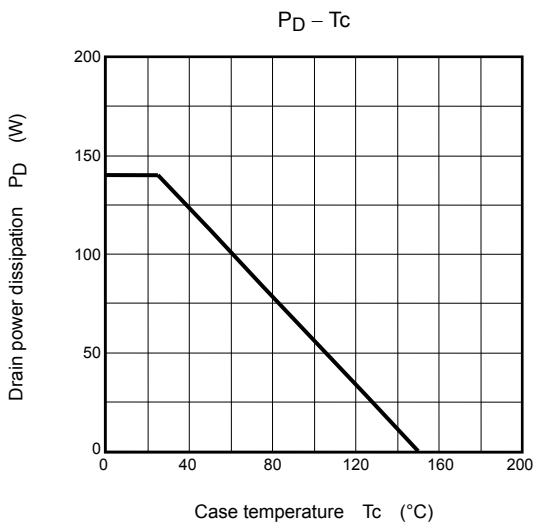
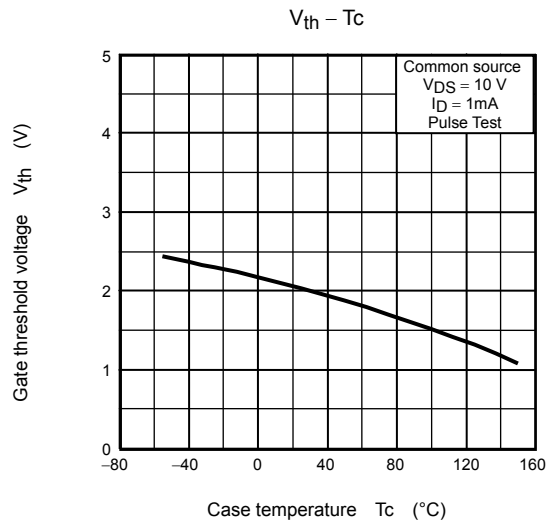
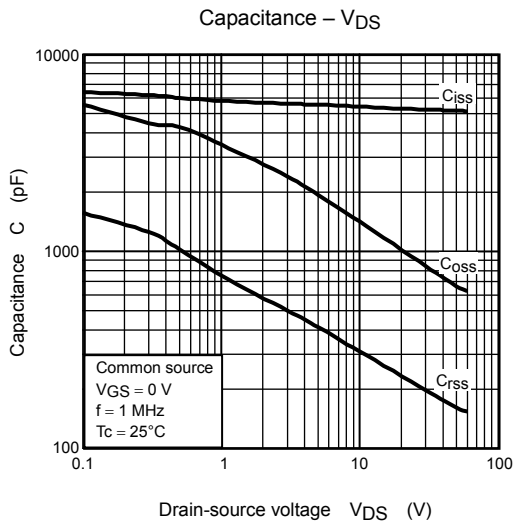
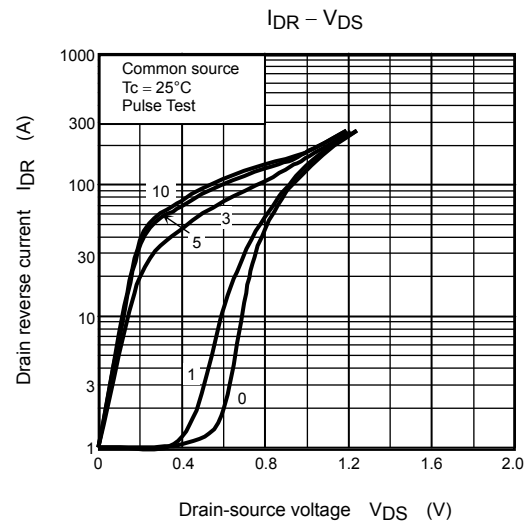
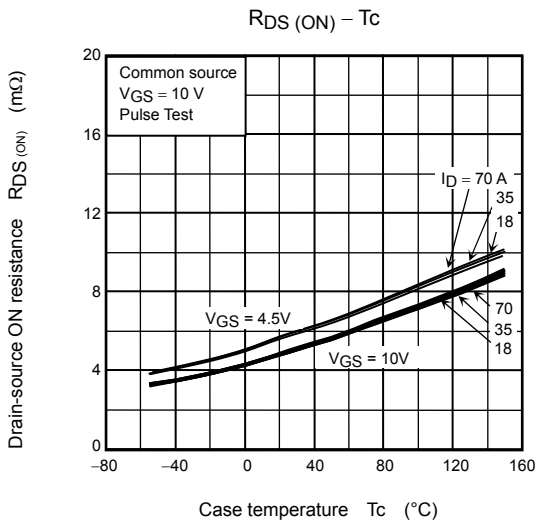
Source-Drain Ratings and Characteristics (Ta = 25°C)

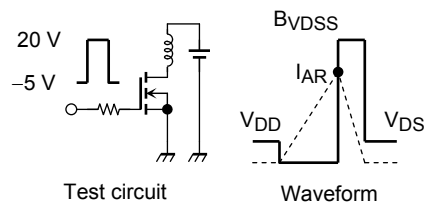
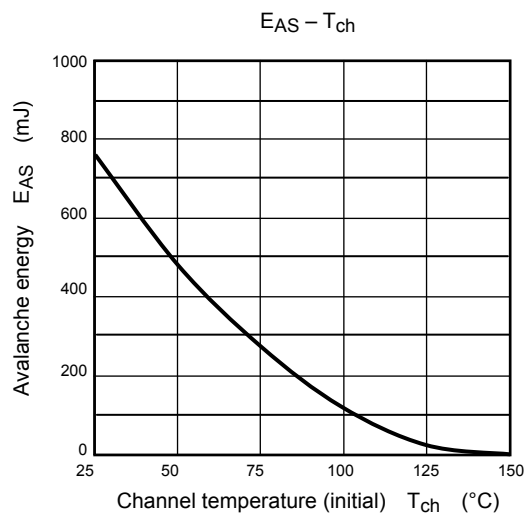
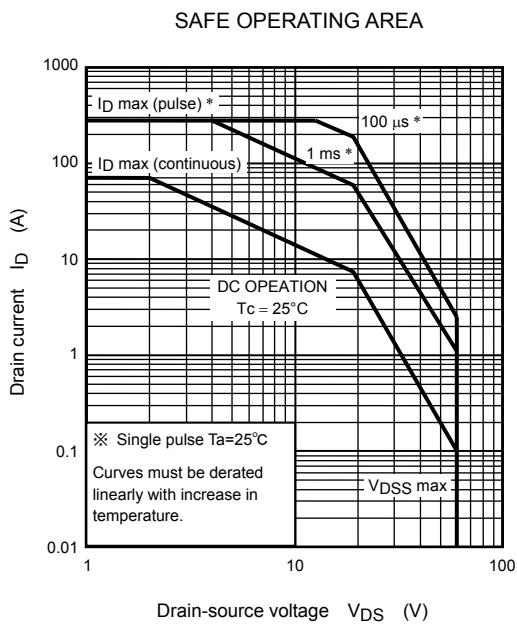
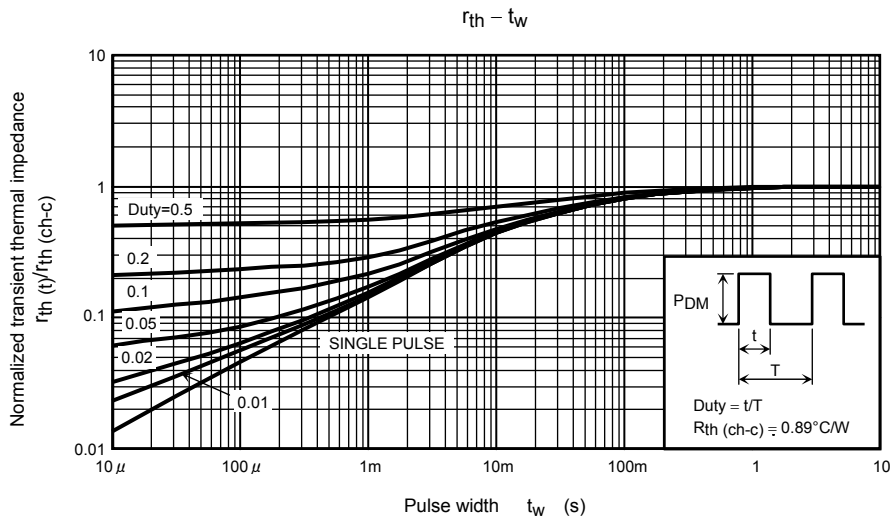
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	70	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	280	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 70 \text{ A}, V_{GS} = 0 \text{ V}$	—	-1.0	-1.2	V
Reverse recovery time	t_{rr}	$I_{DR} = 70 \text{ A}, V_{GS} = 0 \text{ V},$	—	60	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 50 \text{ A}/\mu\text{s}$	—	51	—	nC

Marking









$R_G = 1 \Omega$
 $V_{DD} = 25 \text{ V}, L = 200 \mu\text{H}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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